

B220-13-F(MS) THRU B2200B-13-F(MS)

Product specification





Features

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- For surface mounted applications
- Metal silicon junction, majority carrier conduction
- Low power loss,high efficiency
- Built-in strain relief, ideal for automated placement
- High forward surge current capability
- High temperature soldering guaranteed: 250°C/10 seconds at terminals

Mechanical Data

- Case: JEDEC DO-214AA molded plastic body
- **Terminals**: leads solderable per MIL-STD-750,
- Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.003 ounce, 0.093 grams

Outline	Marking				
Selection of the select	B220B	B230B	B240B		
	B220 -13-F(MS)	B230 -13-F(MS)	B240 -13-F(MS)		
	B250B	B260B	B280B		
	B250 -13-F(MS)	B260 -13-F(MS)	B280 -13-F(MS)		
	B2100B	B2150B	B2200B		
SMB	B2100-13-F(MS)	B2150-13-F(MS)	B2200-13-F(MS)		

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

YFW Catalog Number		SYMBOLS	B220 -13-F(MS)	B230 -13-F(MS)	B240 -13-F(MS)	B250 -13-F(MS)	B260 -13-F(MS)	B280 -13-F(MS)	B2100 -13-F(MS)	B2150 -13-F(MS)	B2200 -13-F(MS)	UNITS
Maximum repetitive peak reverse voltage		Vrrm	20	30	40	50	60	80	100	150	200	VOLTS
Maximum RMS voltage		Vrms	14	21	28	35	42	56	70	105	140	VOLTS
Maximum DC blocking voltage		VDC	20	30	40	50	60	80	100	150	200	VOLTS
Maximum average forward rectified current at TL(see fig.1)		l(AV)	2.0							Amps		
Peak forward surge current												
8.3ms single half sine-wave superimposed on rated load (JEDEC Method)		IFSM	50.0					/	Amps			
Maximum instantaneous forward voltage at 2.0A		Vf	0.55 0.70 0.85 0.95			95	Volts					
Maximum DC reverse current at	Ta=25 ℃		0.5 0.2						mA			
rated DC blocking voltage	Ta=100 ℃	R		10).0	5.0 2.0						
Typical junction capacitance (NOTE 1)		CJ	220 180					pF				
Typical thermal resistance (NOTE 2)		Reja	75.0							℃/W		
Operating junction temperature range		TJ,	-50 to +125 -50 to +150						°C			
Storage temperature range		Тѕтс	-50 to +150						°C			

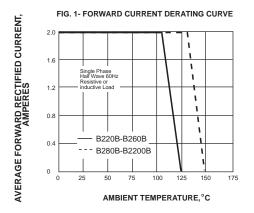
Note:1.Measured at 1MHz and applied reverse voltage of 4.0V D.C. 2.P.C.B. mounted with 0.2x0.2"(5.0x5.0mm) copper pad areas

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Reference News



RATINGS AND CHARACTERISTIC CURVES



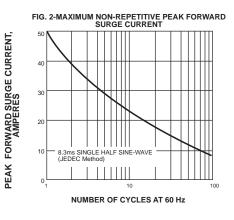
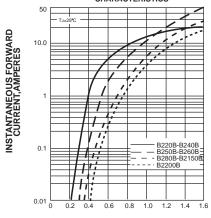


FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS



INSTANTANEOUS FORWARD VOLTAGE,

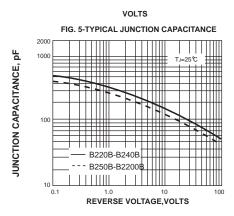
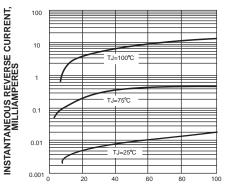
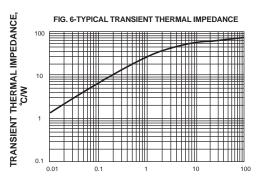


FIG. 4-TYPICAL REVERSE CHARACTERISTICS



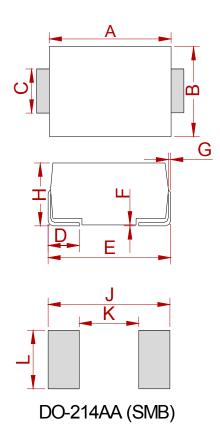
PERCENT OF PEAK REVERSE VOLTAGE,%



t,PULSE DURATION,sec.

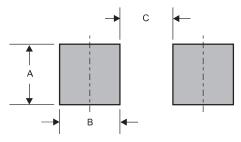


PACKAGE MECHANICAL DATA



	Dimensions						
Ref.	Millin	neters	Inches				
	Min.	Max.	Min.	Max.			
А	4.25	4.75	0.167	0.187			
В	3.30	3.94	0.130	0.155			
С	1.85	2.21	0.073	0.087			
D	0.76	1.52	0.030	0.060			
Е	5.08	5.59	0.200	0.220			
F	0.051	0.203	0.002	0.008			
G	0.15	0.31	0.006	0.012			
Н	2.11	2.44	0.083	0.096			
J	6.80		0.270				
К		2.60		0.100			
L	2.40		0.090				

Suggested solder pad layout



Dimensions in inches and (millimeters)

PACKAGE	А	В	С
SMB	0.078 (2.00)	0.059 (1.50)	0.110 (2.80)

REELSPECIFICATION

P/N	PKG	QTY
B220-13-F(MS) THRU B2200B-13-F(MS)	SMB	3000



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